



September 2014

FDZ1323NZ

Common Drain N-Channel 2.5 V PowerTrench® WL-CSP MOSFET

20 V, 10 A, 13 mΩ

Features

- Max $r_{S1S2(on)}$ = 13 mΩ at $V_{GS} = 4.5$ V, $I_{S1S2} = 1$ A
- Max $r_{S1S2(on)}$ = 13 mΩ at $V_{GS} = 3.8$ V, $I_{S1S2} = 1$ A
- Max $r_{S1S2(on)}$ = 16 mΩ at $V_{GS} = 3.1$ V, $I_{S1S2} = 1$ A
- Max $r_{S1S2(on)}$ = 18 mΩ at $V_{GS} = 2.5$ V, $I_{S1S2} = 1$ A
- Occupies only 3 mm² of PCB area
- Ultra-thin package: less than 0.35 mm height when mounted to PCB
- High power and current handling capability
- HBM ESD protection level > 3.6 kV (Note 3)
- RoHS Compliant

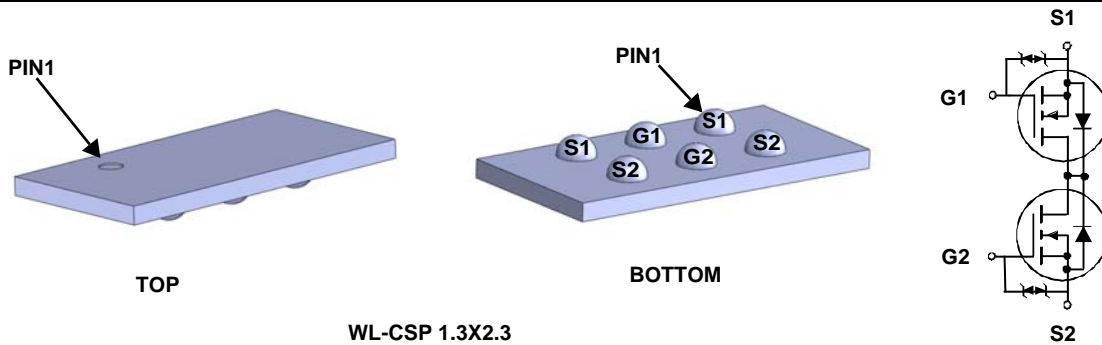


General Description

This device is designed specifically as a single package solution for Li-Ion battery pack protection circuit and other ultra-portable applications. It features two common drain N-channel MOSFETs, which enables bidirectional current flow, on Fairchild's advanced PowerTrench® process with state of the art "low pitch" WLCSP packaging process, the FDZ1323NZ minimizes both PCB space and $r_{S1S2(on)}$. This advanced WLCSP MOSFET embodies a breakthrough in packaging technology which enables the device to combine excellent thermal transfer characteristics, ultra-low profile packaging, low gate charge and low $r_{S1S2(on)}$.

Applications

- Battery management
- Load switch
- Battery protection



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Ratings | Units |
|----------------|---|-------------|------------------|
| V_{S1S2} | Source1 to Source2 Voltage | 20 | V |
| V_{GS} | Gate to Source Voltage | ± 12 | V |
| I_{S1S2} | Source1 to Source2 Current -Continuous $T_A = 25^\circ\text{C}$ (Note 1a) | 10 | A |
| | -Pulsed | 40 | |
| P_D | Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a) | 2 | W |
| | Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1b) | 0.5 | |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 to +150 | $^\circ\text{C}$ |

Thermal Characteristics

| | | | |
|-----------------|---|-----|--------------------|
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 62 | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1b) | 257 | |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|-----------|----------------|-----------|------------|------------|
| EC | FDZ1323NZ | WL-CSP 1.3X2.3 | 7" | 8 mm | 5000 units |

FDZ1323NZ Common Drain N-Channel 2.5 V PowerTrench® WL-CSP MOSFET

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Off Characteristics

| | | | | | | |
|------------|--|---|--|--|----------|---------------|
| I_{S1S2} | Zero Gate Voltage Source1 to Source2 Current | $V_{S1S2} = 16\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| I_{GSS} | Gate to Source Leakage Current | $V_{GS} = \pm 12\text{ V}, V_{S1S2} = 0\text{ V}$ | | | ± 10 | μA |

On Characteristics

| | | | | | | |
|----------------|---|---|-----|-----|-----|------------|
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS} = V_{S1S2}, I_{S1S2} = 250\ \mu\text{A}$ | 0.4 | 0.9 | 1.2 | V |
| $r_{S1S2(on)}$ | Static Source1 to Source2 On Resistance | $V_{GS} = 4.5\text{ V}, I_{S1S2} = 1\text{ A}$ | 4.5 | 9.7 | 13 | m Ω |
| | | $V_{GS} = 3.8\text{ V}, I_{S1S2} = 1\text{ A}$ | 5.5 | 10 | 13 | |
| | | $V_{GS} = 3.1\text{ V}, I_{S1S2} = 1\text{ A}$ | 7 | 11 | 16 | |
| | | $V_{GS} = 2.5\text{ V}, I_{S1S2} = 1\text{ A}$ | 8 | 13 | 18 | |
| | | $V_{GS} = 4.5\text{ V}, I_{S1S2} = 1\text{ A}, T_J = 125^\circ\text{C}$ | | 13 | 20 | |
| g_{FS} | Forward Transconductance | $V_{S1S2} = 5\text{ V}, I_{S1S2} = 1\text{ A}$ | | 9 | | S |

Dynamic Characteristics

| | | | | | | |
|-----------|------------------------------|--|--|------|------|----|
| C_{iss} | Input Capacitance | $V_{S1S2} = 10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$ | | 1545 | 2055 | pF |
| C_{oss} | Output Capacitance | | | 269 | 405 | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 252 | 380 | pF |

Switching Characteristics

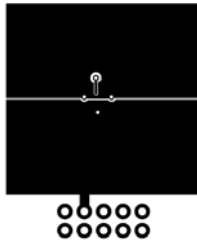
| | | | | | | |
|--------------|---------------------------------|--|--|-----|----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{S1S2} = 10\text{ V}, I_{S1S2} = 1\text{ A},$ $V_{GS} = 4.5\text{ V}, R_{GEN} = 6\ \Omega$ | | 12 | 22 | ns |
| t_r | Rise Time | | | 13 | 23 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 34 | 54 | ns |
| t_f | Fall Time | | | 13 | 23 | ns |
| Q_g | Total Gate Charge | | | 17 | 24 | nC |
| Q_{gs} | Gate to Source1 Gate Charge | $V_{S1S2} = 10\text{ V}, I_{S1S2} = 1\text{ A},$ $V_{G1S1} = 4.5\text{ V}, V_{G2S2} = 0\text{ V}$ | | 1.9 | | nC |
| Q_{gd} | Gate to Source2 "Miller" Charge | | | 5.4 | | nC |

Source1 to Source2 Diode Characteristics

| | | | | | | |
|-----------|---|--|--|-----|-----|---|
| I_{fss} | Maximum Continuous Source1 to Source2 Diode Forward Current | | | 1 | A | |
| V_{fss} | Source1 to Source2 Diode Forward Voltage | $V_{G1S1} = 0\text{ V}, V_{G2S2} = 4.5\text{ V},$ $I_{fss} = 1\text{ A}$ (Note 2) | | 0.6 | 1.2 | V |

Notes:

- $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 62 °C/W when mounted on a 1 in² pad of 2 oz copper.



b. 257 °C/W when mounted on a minimum pad of 2 oz copper.

- Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.

- The diode connected between the gate and source serves only protection against ESD. No gate overvoltage rating is implied.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

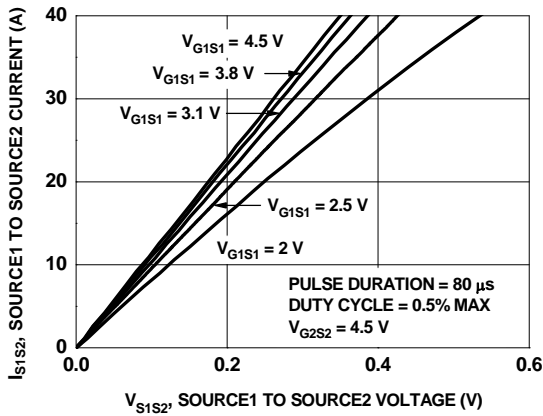


Figure 1. On-Region Characteristics

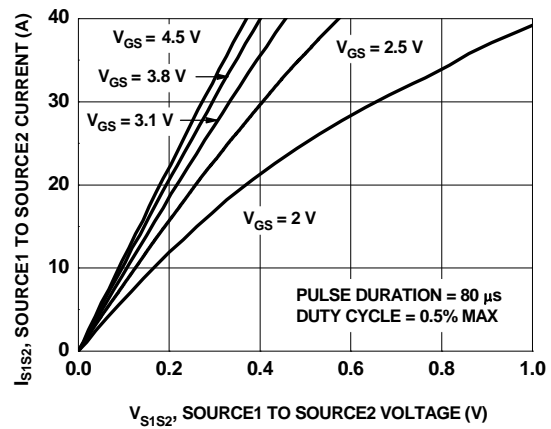


Figure 2. On-Region Characteristics

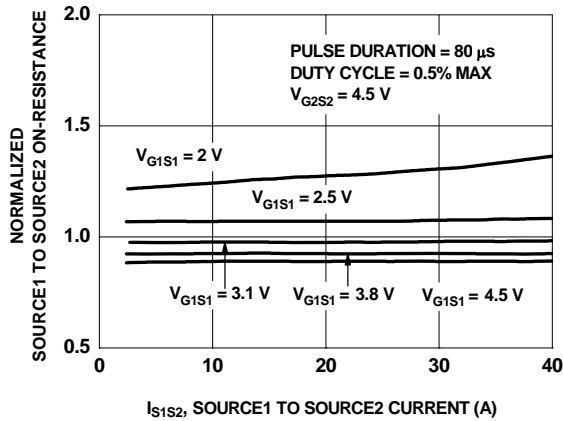


Figure 3. Normalized On-Resistance vs Source1 to Source2 Current and Gate Voltage

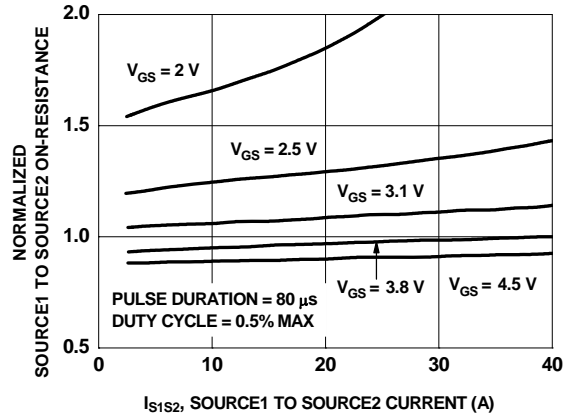


Figure 4. Normalized On-Resistance vs Source1 to Source2 Current and Gate Voltage

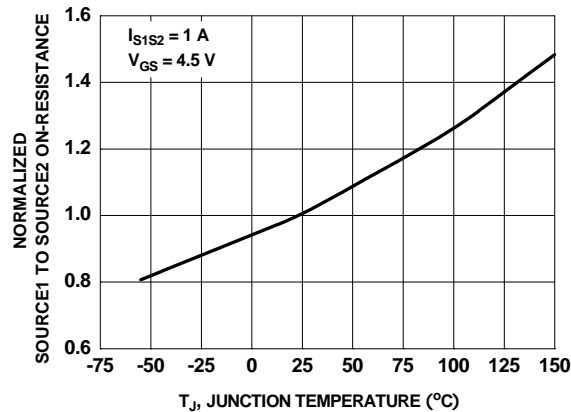


Figure 5. Normalized On Resistance vs Junction Temperature

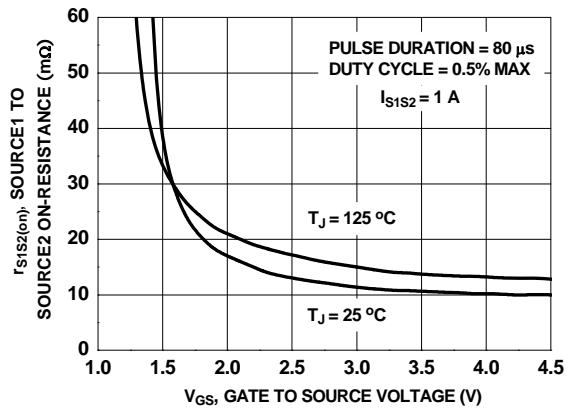


Figure 6. On Resistance vs Gate to Source Voltage

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

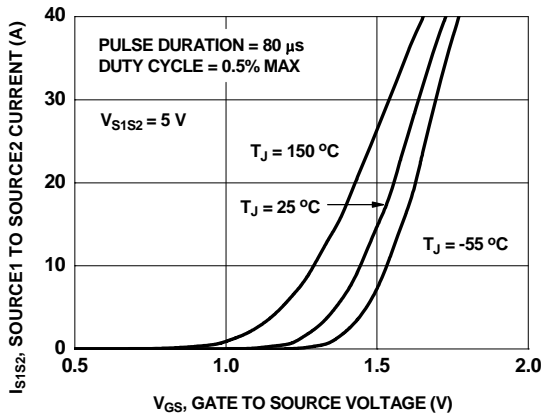


Figure 7. Transfer Characteristics

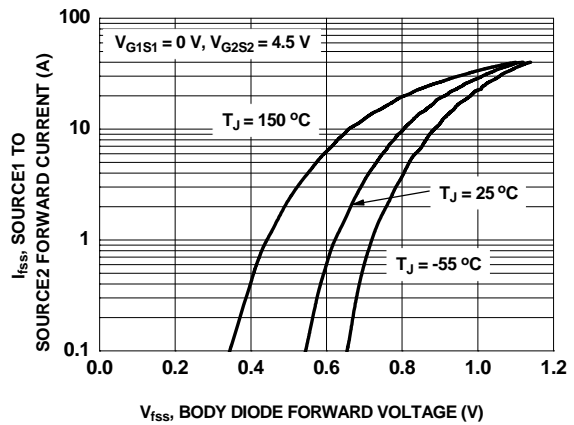


Figure 8. Source1 to Source2 Diode Forward Voltage vs Source Current

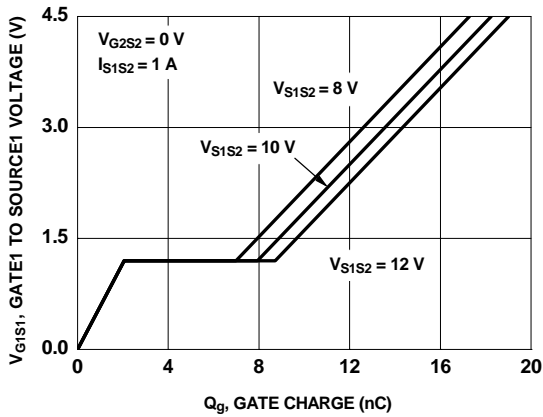


Figure 9. Gate Charge Characteristics

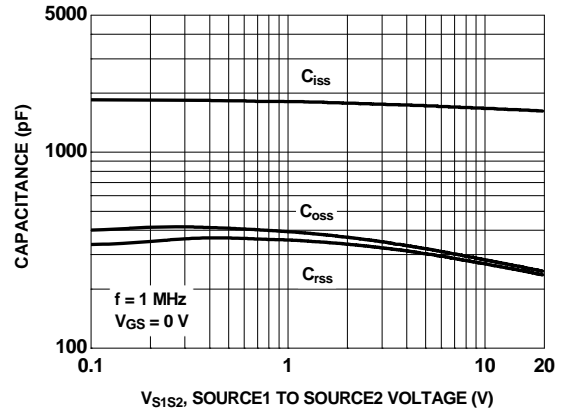


Figure 10. Capacitance vs Source1 to Source2 Voltage

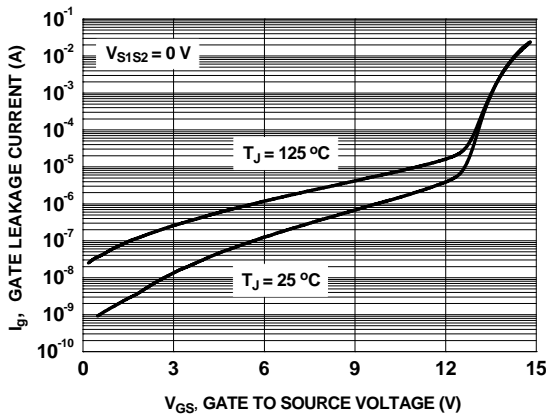


Figure 11. Gate Leakage Current vs Gate to Source Voltage

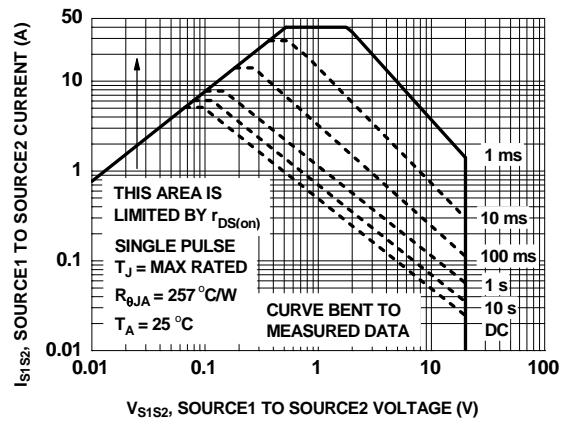
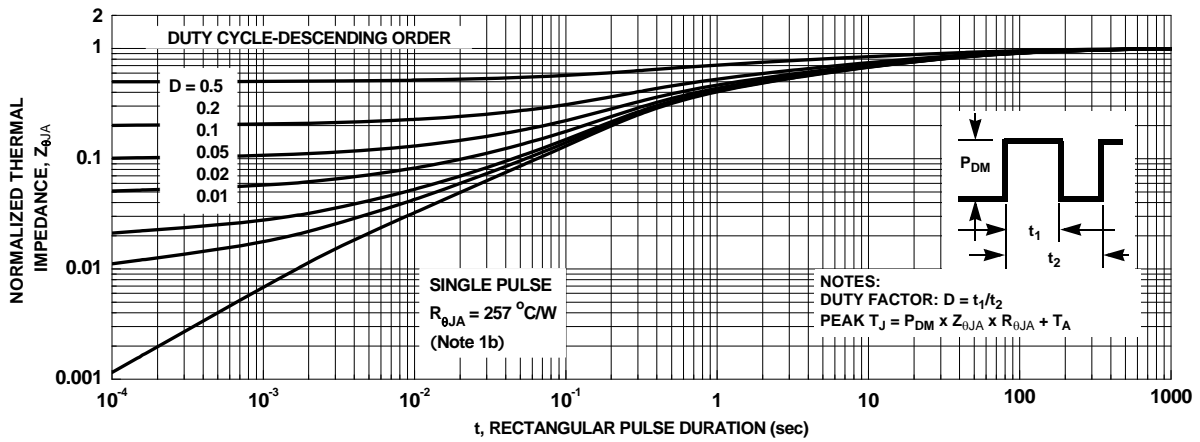
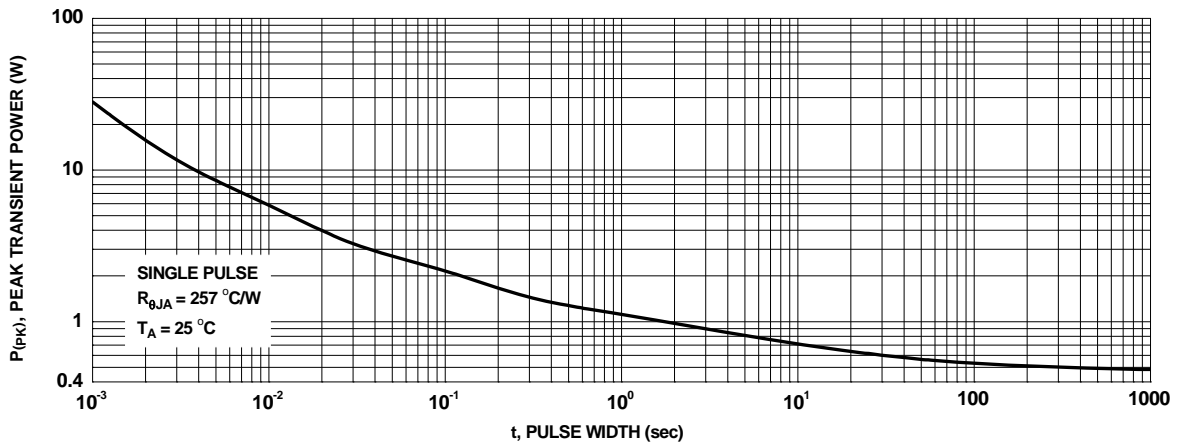
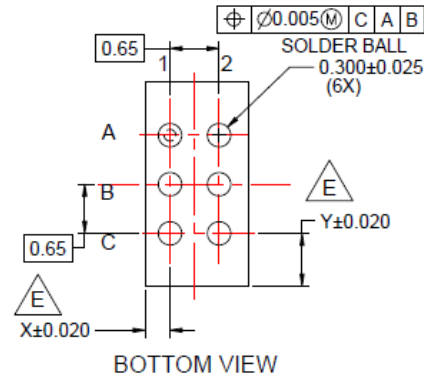
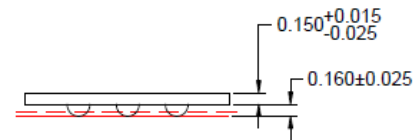
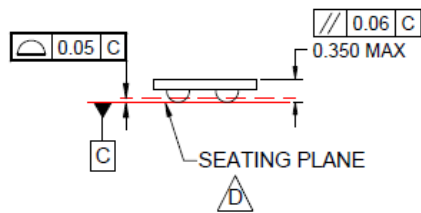
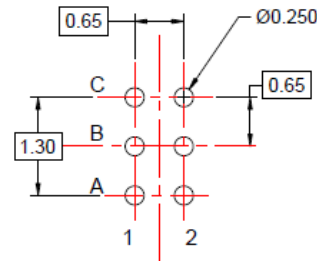
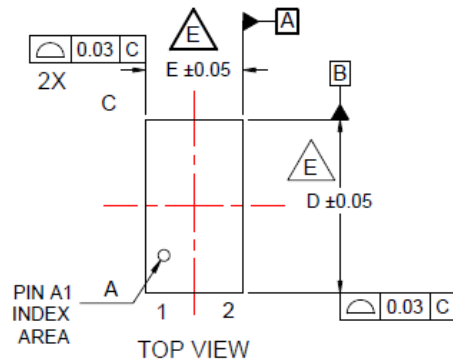


Figure 12. Forward Bias Safe Operating Area

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted



Dimensional Outline and Pad Layout



NOTES:

- A. NO JEDEC REGISTRATION APPLIES.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCE PER ASME Y14.5M, 2009.
- D. DATUM C IS DEFINED BY THE SPHERICAL CROWNS OF THE BALLS.
- E. FOR DIMENSIONS D, E, X, AND Y SEE PRODUCT DATA SHEET.
- F. MKT-UC006ABREV2
- G. FOR PIN-OUT ASSIGNMENT, REFER TO DATA SHEET.



Pin Definitions:

| | | |
|--------|---------|---------|
| Gate | Source1 | Source2 |
| B1, B2 | A1, C1 | A2, C2 |

Product Specific Dimensions:

| | | | |
|--------|--------|----------|---------|
| D | E | X | Y |
| 2.3 mm | 1.3 mm | 0.315 mm | 0.49 mm |


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